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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/691,055
		Filing Date	October 22, 2003
		First Named Inventor	Kryliouk et al.
		Art Unit	
Examiner Name			
Sheet 1	of 2	Attorney Docket Number	5853-414

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SWC		NIKISHIN et al., "High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia," Applied Physics Letters, 75:2073-2075, 1999	
		ZHANG et al., "Enhanced optical emission from GaN films grown on a silicon substrate," Applied Physics Letters, 74:1984-1986, 1999	
		LINTHICUM et al., "PROCESS ROUTES FOR LOW DEFECT-DENSITY GAN ON VARIOUS SUBSTRATES EMPLOYING PENDEO-EPITAXIAL GROWTH TECHNIQUES," MRS Internet J. Nitride Semicond. Res. 4S1, G4.9, 1999	
		STRITTMATTER et al., "Low-pressure metal organic chemical vapor deposition of GaN on silicon(111) substrates using an AlAs nucleation layer," Applied Physics Letters, 74:1242-1244, 1999	
		SANCHEZ-GARCIA et al., "Ultraviolet electroluminescence in GaN/AlGaIn single-heterojunction light-emitting diodes grown on Si(111)," Journal of Applied Physics, 87:1569-1571, 2000	
		NISHIMURA et al., "Growth of GaN on Si substrates-roles of BP thin layer," Optical Materials, 19:223-228, 2002.	
		NISHIMURA et al., "Low temperature growth interface for growing Boron Monophosphide on Si substrates," Applied Surface Science, 159-160:288-291, 2000.	
		NISHIMURA et al., "Growth of c-GaN on Si(100)," Materials Science and Engineering," B82:25-26, 2001.	
		IZUMIYA et al., "Growth of BP and GaN/BP heterostructures," Proceedings of the 19th International Symposium on Gallium Arsenide and Related Compounds, 157-162, 1993.	
SWC		NISHINAGA et al., "Effect of Growth Parameters on the Epitaxial Growth of BP on Si Substrate," Japanese Journal of Applied Physics, 14:753-760, 1975.	

Examiner Signature	CRANE	Date Considered	9/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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SWC		LANDOLT-BORNSTEIN, "Semiconductors," 3:14-28 and 43-50.	
		WELKER et al., "Solid State Physics," Group III-Group V Compounds, 1-78, 1956.	
		Johnson, S., "CHAPTER 3 GROWTH OF BP BY CVD" Ph.D. Thesis, 2001.	
SWC		TERASHIMA et al., "Proceedings of the 8th International Symposium on Silicon Materials Science and Technology," 2:44-45, 1998.	

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